

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2002-093804

(43)Date of publication of application : 29.03.2002

---

(51)Int.Cl. H01L 21/316  
C23C 16/40  
H01L 29/78

---

(21)Application number : 2000-282198 (71)Applicant : TRI CHEMICAL LABORATORY INC

(22)Date of filing : 18.09.2000 (72)Inventor : MACHIDA HIDEAKI  
HOSHINO ASAOKO

---

## (54) MATERIAL FOR FORMING HAFNIUM-BASED OXIDE FILM

### (57)Abstract:

PROBLEM TO BE SOLVED: To efficiently provide a technique for forming a neat hafnium-based film.

SOLUTION: A compound which is expressed by a chemical formula (R<sub>1</sub>R<sub>2</sub>N)<sub>4</sub> Hf is used.

---

### LEGAL STATUS

[Date of request for examination] 22.11.2001

[Date of sending the examiner's decision of rejection] 26.11.2002

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3409290

[Date of registration] 20.03.2003

[Number of appeal against examiner's decision of rejection] 2002-24698

[Date of requesting appeal against examiner's decision of rejection] 24.12.2002

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office